

SPTECH Silicon NPN Power Transistor

2SC2437

DESCRIPTION

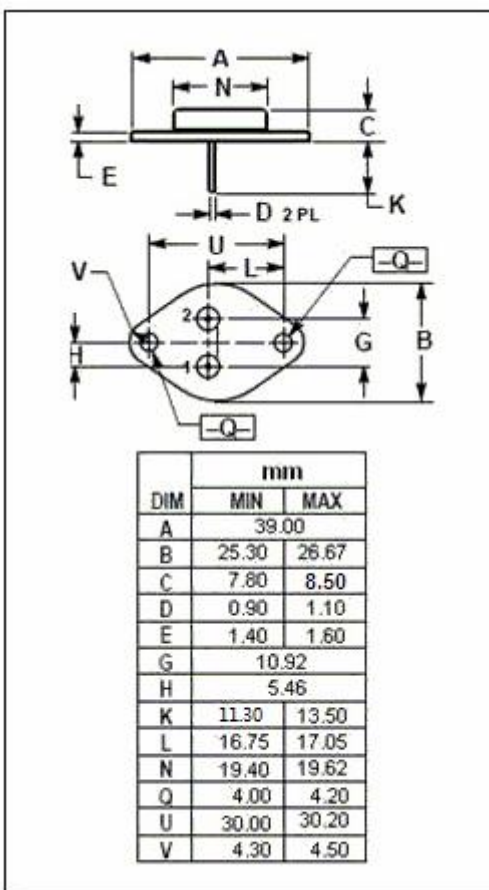
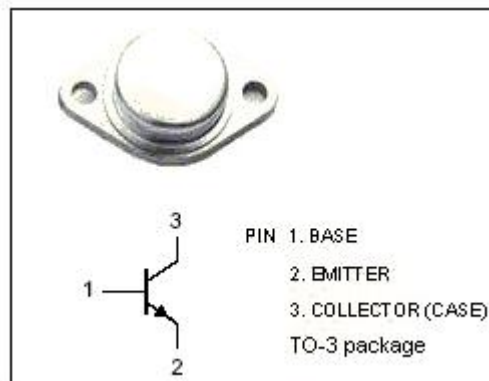
- Collector-Emitter Sustaining Voltage-
: $V_{CEO(SUS)} = 400V$ (Min)
- High Switching Speed

APPLICATIONS

- Switching regulators
- DC-DC convertor
- Solid state relay
- General purpose power amplifiers

ABSOLUTE MAXIMUM RATINGS($T_a=25^\circ C$)

SYMBOL	PARAMETER	MAX	UNIT
V_{CBO}	Collector-Base Voltage	450	V
V_{CEO}	Collector-Emitter Voltage	400	V
V_{EBO}	Emitter-Base Voltage	7	V
I_C	Collector Current-Continuous	7	A
I_B	Base Current-Continuous	2	A
P_C	Collector Power Dissipation @ $T_C=25^\circ C$	100	W
T_j	Junction Temperature	150	$^\circ C$
T_{stg}	Storage Temperature Range	-55~150	$^\circ C$



SPTECH Silicon NPN Power Transistor**2SC2437****ELECTRICAL CHARACTERISTICS****T_C=25°C unless otherwise specified**

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
V _{CE(SUS)}	Collector-Emitter Sustaining Voltage	I _C =50mA; I _B = 0	400			V
V _{(BR)CBO}	Collector-Base Breakdown Voltage	I _C = 1mA; I _E = 0	450			V
V _{(BR)EBO}	Emitter-Base Breakdown Voltage	I _E = 0.1mA; I _C = 0	7			V
V _{CE(sat)}	Collector-Emitter Saturation Voltage	I _C = 7A; I _B = 1.4A			1.5	V
V _{BE(sat)}	Base-Emitter Saturation Voltage	I _C = 7A; I _B = 1.4A			1.2	V
I _{CBO}	Collector Cutoff Current	V _{CB} = 450V; I _E = 0			1.0	mA
I _{EBO}	Emitter Cutoff Current	V _{EB} = 7V; I _C = 0			0.1	mA
h _{FE}	DC Current Gain	I _C = 3A; V _{CE} = 4V	10			